

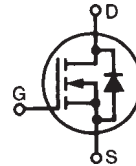
# HiPerFET™ Power MOSFETs Q-Class

**IXFK 24N120Q2**  
**IXFX 24N120Q2**

$V_{DSS} = 1200\text{ V}$   
 $I_{D25} = 24\text{ A}$   
 $R_{DS(on)} = 0.65\ \Omega$

$t_{rr} \leq 300\text{ ns}$

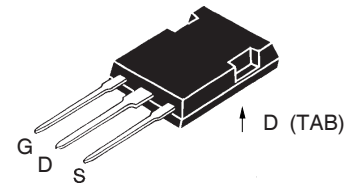
N-Channel Enhancement Mode  
Avalanche Rated, High  $dv/dt$ , Low  $Q_g$   
Low intrinsic  $R_g$ , low  $t_{rr}$



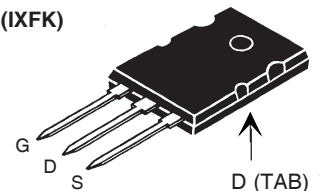
## Preliminary Data Sheet

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	1200	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	24	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	96	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	12	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	30	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	4.0	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	830	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	TO-264	0.9/6 Nm/lb.in.
Weight		PLUS-247	6 g
		TO-264	10 g

### PLUS247™ (IXFX)



### TO-264 AA (IXFK)



G = Gate  
S = Source

D = Drain  
TAB = Drain

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 3\text{ mA}$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8\text{ mA}$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 200\text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$			50 $\mu\text{A}$
	$V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$			2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			0.65 $\Omega$

### Features

- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

### Advantages

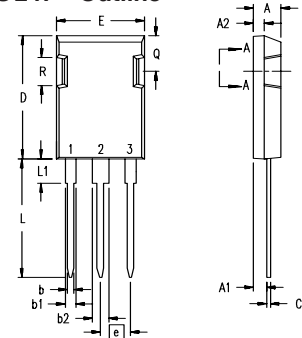
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 20\text{ V}$ ; $I_D = 0.5 \cdot I_{D25}$ , pulse test	15	25	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		8200	pF
$C_{oss}$			560	pF
$C_{rss}$			110	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1.0\ \Omega$ (External),		22	ns
$t_r$			13	ns
$t_{d(off)}$			60	ns
$t_f$			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		180	nC
$Q_{gs}$			45	nC
$Q_{gd}$			80	nC
$R_{thJC}$	TO-264		0.15	K/W
$R_{thCK}$			0.15	K/W

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			24 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			96 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ , $-di/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 100\text{ V}$		1	300 ns
$Q_{RM}$			10	$\mu\text{C}$
$I_{RM}$				A

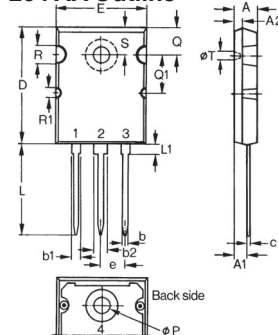
### PLUS247™ Outline



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L <sub>1</sub>	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

### TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A <sub>1</sub>	2.54	2.89	.100	.114
A <sub>2</sub>	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b <sub>1</sub>	2.39	2.69	.094	.106
b <sub>2</sub>	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L <sub>1</sub>	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q <sub>1</sub>	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R <sub>1</sub>	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344